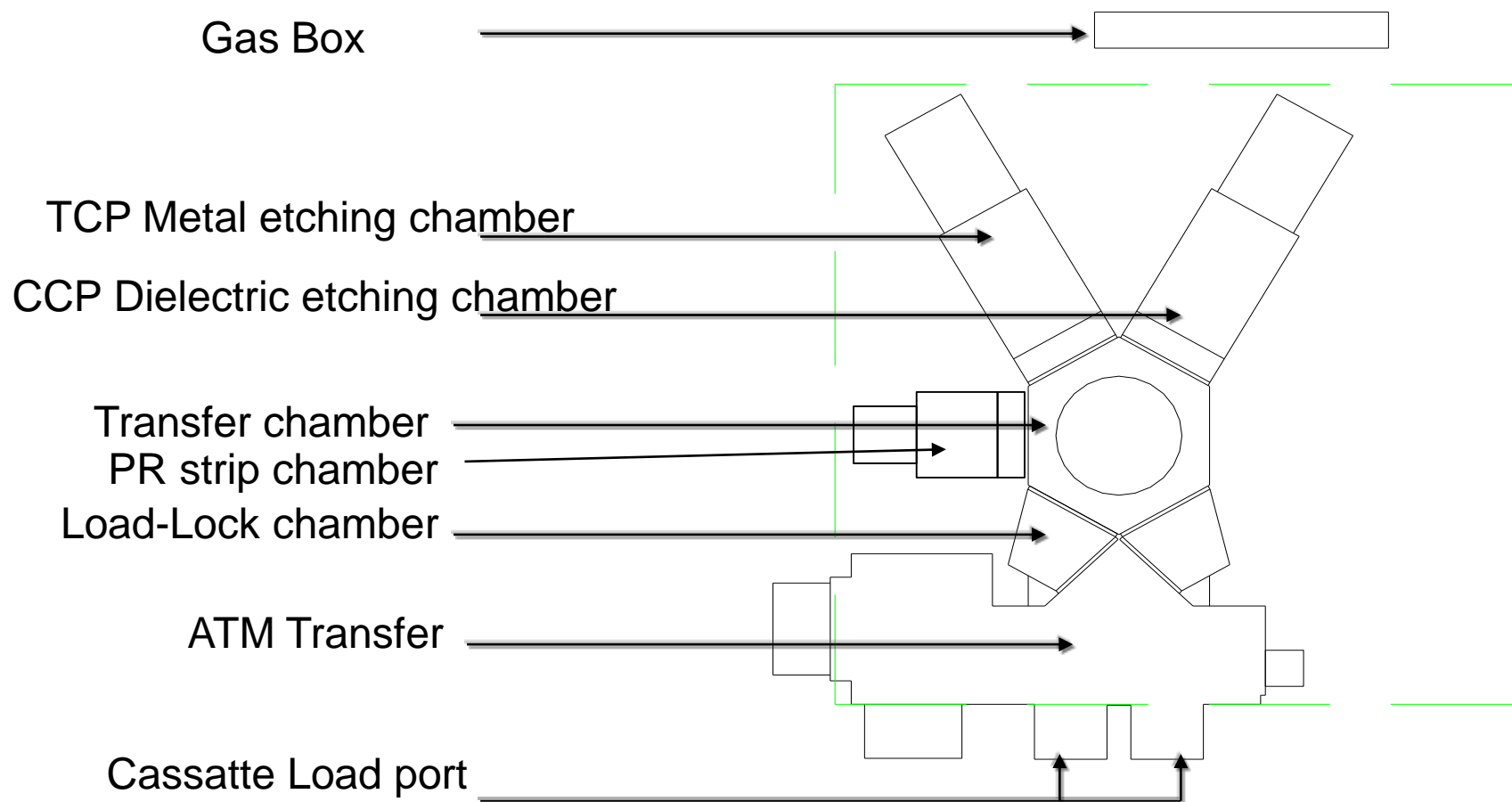


# 8 inch Back-End Lam Etcher

## Technical Information

# Overview



# Process Module



## TCP Metal etching chamber :

Process condition: Nano scale

Process pressure: 8mtorr~100mtorr

Process gas:  $\text{Cl}_2$ 、 $\text{BCl}_3$ 、 $\text{HBr}$ 、 $\text{Ar}$ 、 $\text{CH}_2\text{F}_2$ 、 $\text{CH}_4$ 、 $\text{O}_2$  etc..

RF Top : 13.56MHz

RF Bot : 13.56MHz

Process temperature: 60°C

# Process Module



## CCP Dielectric etching chamber :

Process condition: Nano scale

Process pressure: 8mtorr~100mtorr

Process gas: CO、C<sub>4</sub>F<sub>8</sub>、C<sub>4</sub>F<sub>6</sub>、Ar、CF<sub>4</sub>、O<sub>2</sub>etc..

RF Top :27MHz

RF Bot :2MHz

Process temperature:140°C

# Process Module



## PR Strip Chamber :

Process pressure:8mtorr~100mtorr

Process gas: $N_2$ 、DI vapor、 $O_2$ ..

Process temperature:250°C

RF frequency:2.45GHz Microwave plasma.